

DCR1574SY

Phase Control Thyristor

Replaces January 2000 version, DS4400-3.0

DS4400-4.0 July 2001

FEATURES

- Double Side Cooling.
- High Surge Capability.
- High Current.
- Fatigue Free.

APPLICATIONS

- High Power Drives.
- High Voltage Power Supplies.
- DC Motor Control.

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages VDRM VRRM	Conditions
DCR1574SY28 DCR1574SY27 DCR1574SY26 DCR1574SY25 DCR1574SY24	2800 2700 2600 2500 2400	$\begin{split} & T_{vj} = 0^{\circ} \text{ to } 125^{\circ}\text{C}, \\ & I_{DRM} = I_{RRM} = 300\text{mA}, \\ & V_{DRM}, V_{RRM} t_{p} = 10\text{ms}, \\ & V_{DSM} \& V_{RSM} = \\ & V_{DRM} \& V_{RRM} + 100V \\ & respectively \end{split}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1574SY25

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

KEY PARAMETERS

 V_{DRM} 2800V 3419A 1_{T(AV)} 54500A dVdt 1000V/ μ s dI/dt 300A/ μ s

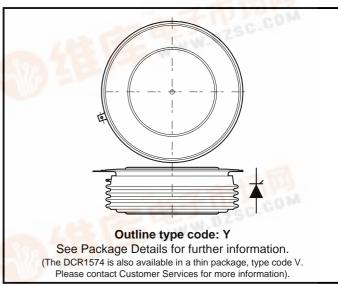


Fig. 1 Package outline





CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units		
Double Sid	Double Side Cooled					
I _{T(AV)}	Mean on-state current	Half wave resistive load	3419	А		
I _{T(RMS)}	RMS value	-	5370	Α		
I _T	Continuous (direct) on-state current	-	4836	Α		
Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load	2197	А		
I _{T(RMS)}	RMS value	-	3451	Α		
Ι _τ	Continuous (direct) on-state current	-	2857	Α		

CURRENT RATINGS

 $T_{case} = 80^{\circ}C$ unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	2667	А			
I _{T(RMS)}	RMS value	-	4189	А			
I _T	Continuous (direct) on-state current	-	3680	А			
Single Side Cooled (Anode side)							
I _{T(AV)}	Mean on-state current	Half wave resistive load	1680	А			
I _{T(RMS)}	RMS value	-	2640	А			
I _T	Continuous (direct) on-state current	-	2140	А			



SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	43.8	kA
l²t	I ² t for fusing	V _R = 50% V _{RRM} - 1/4 sine	9.59 x 10 ⁶	A ² s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	54.5	kA
l²t	I ² t for fusing	$V_R = 0$	14.85 x 10 ⁶	A ² s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - junction to case	Double side cooled	dc	-	0.0095	°C/W
		Single side cooled	Anode dc	-	0.019	°C/W
			Cathode dc	-	0.019	°C/W
R _{th(c-h)}		Clamping force 50.0kN with mounting compound	Double side	-	0.002	°C/W
			Single side	-	0.004	°C/W
T _{vj}	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	150	°C
-	Clamping force			45.0	55.0	kN



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		•	300	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% $V_{DRM} T_j = 125^{\circ}C$.		-	1000	V/μs
		From 80% V _{DRM}	Repetitive 50Hz	-	250	A/μs
dl/dt	Rate of rise of on-state current	Gate source 20V, 10Ω t _r < 0.5 μ s. To JEDEC RS397	Non-repetitive	-	500	A/μs
$V_{T(TO)}$	Threshold voltage	At T _{vj} = 125°C		-	0.883	٧
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.11	mΩ
t _{gd}	Delay time	$V_D = 67\% \ V_{DRM}$, Gate source 30V, 15 Ω Rise time 0.5 μ s, $T_j = 25^{\circ}C$		-	2	μs
I _L	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		-	350	mA
I _H	Holding current	$T_j = 25^{\circ}C, R_{g-k} = \infty$		-	100	mA
t _q	Turn-off time	$I_T = 400A$, $t_p = 1ms$, $T_j = 125$ °C, $V_{RM} = 50V$, $dI_{RR}/dt = 40A/\mu s$, $V_{DR} = 900V$, $dV_{DR}/dt = 40V/\mu s$ linear		400	-	μs

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions		Units
$V_{\rm GT}$	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3.0	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	300	mA
V _{GD}	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	0.25	V
V _{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V _{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	٧
V _{RGM}	Peak reverse gate voltage		5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	А
P _{GM}	Peak gate power	See figs. 7 and 8, gate characteristics table	150	W
$P_{G(AV)}$	Mean gate power		10	W



CURVES

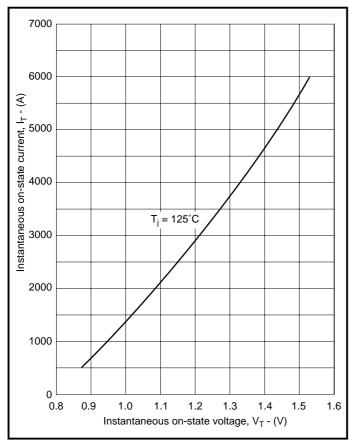


Fig.2 Maximum (limit) on-state characteristics

V_{TM} Equation:

$$V_{TM} = A + BIn (I_T) + C.I_T + D. \sqrt{I_T}$$

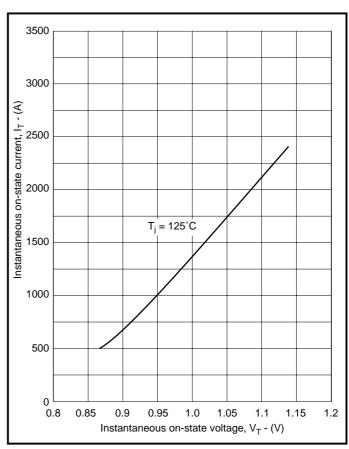


Fig.3 Maximum (limit) on-state characteristics

Where A = 1.328994

B = -0.1381631

 $C = 3.565973 \times 10^{-6}$

D = 0.01786171

These values are valid for $T_j = 125^{\circ}C$ for $I_T 500A$ to 6000A



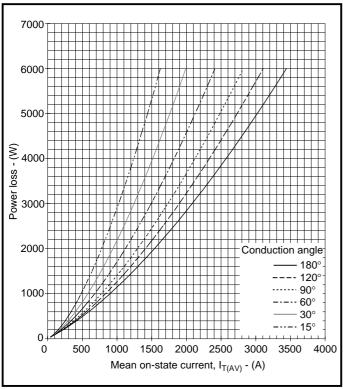


Fig.4 Sine wave power dissipation curves

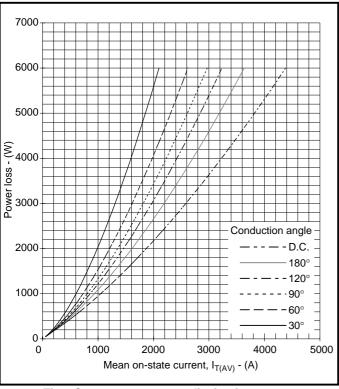


Fig.6 Square wave power dissipation curves

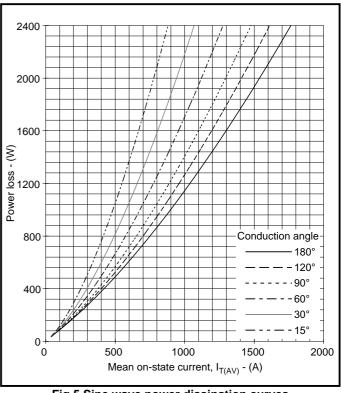


Fig.5 Sine wave power dissipation curves

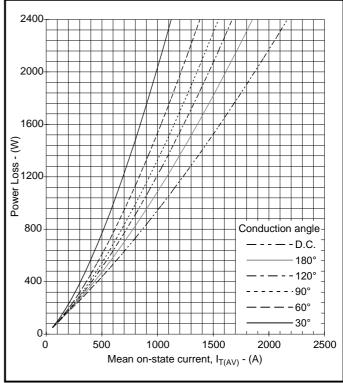


Fig.7 Square wave power dissipation curves



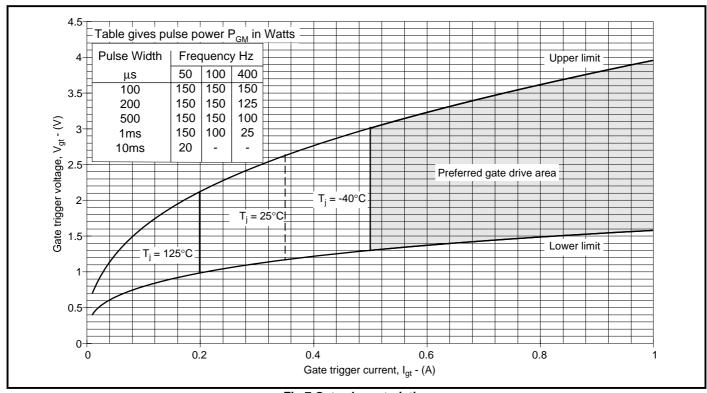


Fig.7 Gate characteristics

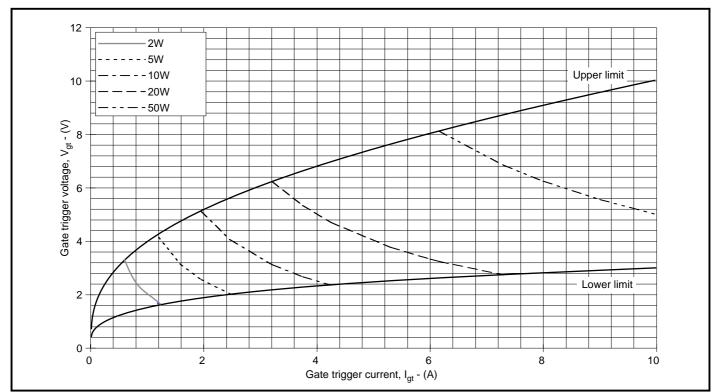
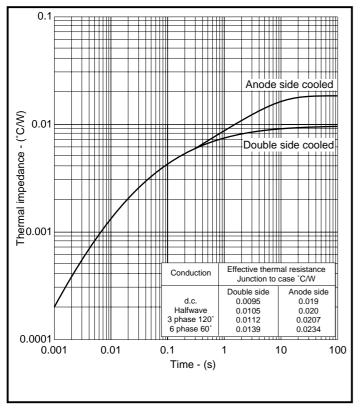
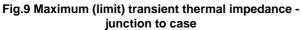


Fig.8 Gate characteristics







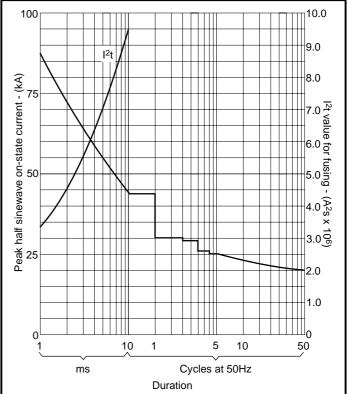
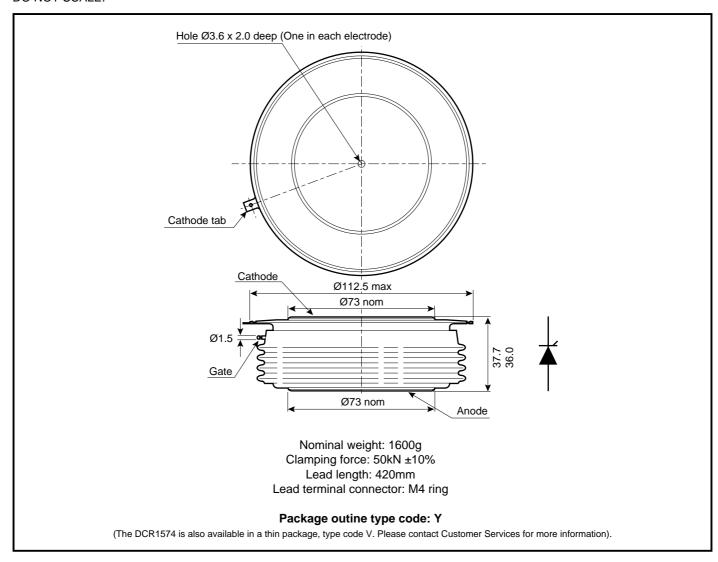


Fig.10 Surge (non-repetitive on-state current vs time



PACKAGE DETAILS

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



http://www.dynexsemi.com

e-mail: power solutions@dynexsemi.com

HEADQUARTERS OPERATIONS DYNEX SEMICONDUCTOR LTD

Doddington Road, Lincoln. Lincolnshire. LN6 3LF. United Kingdom. Tel: 00-44-(0)1522-500500 Fax: 00-44-(0)1522-500550

DYNEX POWER INC.

99 Bank Street, Suite 410, Ottawa, Ontario, Canada, K1P 6B9 Tel: 613.723.7035 Fax: 613.723.1518 Toll Free: 1.888.33.DYNEX (39639) CUSTOMER SERVICE CENTRES

Mainland Europe Tel: +33 (0)1 58 04 91 00. Fax: +33 (0)1 46 38 51 33

North America Tel: (613) 723-7035. Fax: (613) 723-1518.

UK, Scandinavia & Rest Of World Tel: +44 (0)1522 500500. Fax: +44 (0)1522 500020

SALES OFFICES

Mainland Europe Tel: +33 (0)1 58 04 91 00. Fax: +33 (0)1 46 38 51 33

North America Tel: (613) 723-7035. Fax: (613) 723-1518. Toll Free: 1.888.33.DYNEX (39639) /

Tel: (949) 733-3005. Fax: (949) 733-2986.

UK, Scandinavia & Rest Of World Tel: +44 (0)1522 500500. Fax: +44 (0)1522 500020

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